

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AJT030** is Designed for

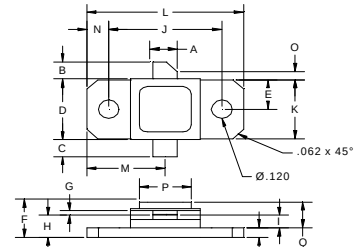
FEATURES:

- Input Matching Network
- **OmniGold™** Metalization System

MAXIMUM RATINGS

I_C	3.5 A
V_{CC}	40 V
P_{DISS}	75 W @ T _C ≤ 85 °C
T_J	-65 °C to +250 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	2.2 °C/W

PACKAGE STYLE .400 2L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.140 / 3.56	
B	.110 / 2.80	
C	.110 / 2.80	
D	.395 / 10.03	.407 / 10.34
E	.193 / 4.90	
F		.230 / 5.84
G	.003 / 0.08	.006 / 0.15
H	.118 / 3.00	.131 / 3.33
I	.063 / 1.60	
J	.650 / 16.51	
K	.386 / 9.80	
L	.900 / 22.86	
M	.450 / 11.43	
N	.125 / 3.18	
O	.050 / 1.27	
P	.405 / 10.29	
Q	.170 / 4.32	
R	.062 / 1.58	

ORDER CODE: ASI10546

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 10 mA	55			V
BV_{CER}	I _C = 20 mA R _{BE} = 10 Ω	55			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
I_{CES}	V _{CE} = 35 V			5.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	15		150	---
P_G	V _{CC} = 50 V P _{OUT} = 30 W f = 960 - 1215 MHz	7.8			dB
η_C		40			%